

EN: This Datasheet is presented by the manufacturer.

Please visit our website for pricing and availability at <u>www.hestore.hu</u>.

3.2x1.6mm PHOTOTRANSISTOR

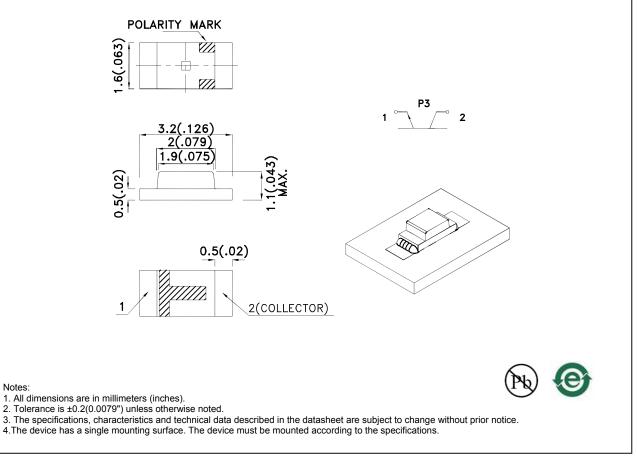
Part Number: KP-3216P3C

Features

- 3.2mmx1.6mm SMT LED, 1.1mm thickness.
- Mechanically and spectrally matched to infrared emitting LED lamp.
- Package : 2000pcs / reel.
- Moisture sensitivity level : level 3.
- RoHS compliant.

Description Made with NPN silicon phototransistor chips.

Package Dimensions



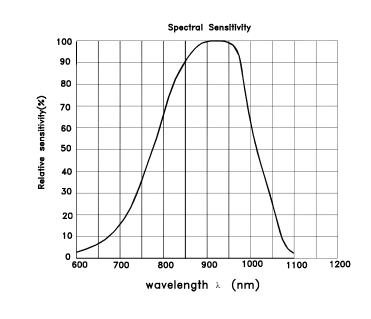
SPEC NO: DSAA4436 APPROVED: WYNEC REV NO: V.13B CHECKED: Allen Liu DATE: SEP/25/2012 DRAWN: D.M.Su PAGE: 1 OF 4 ERP: 1203000370

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
VBR CEO	Collector-to-Emitter Breakdown Voltage	30			V	lc=100uA Ee=0mW/c m [°]
VBR ECO	Emitter-to-Collector Breakdown Voltage	5			V	l∈=100uA Ee=0mW/c mঁ
VCE (SAT)	Collector-to-Emitter Saturation Voltage			0.8	v	lc=2mA Ee=20mW/c mឺ
I CEO	Collector Dark Current			100	nA	Vce=10V Ee=0mW/c m ^²
Tr	Rise Time (10% to 90%)		15		us	Vce = 5V Ic=1mA RL=1000Ω
Tf	Fall Time (90% to 10%)		15		us	
I (ON)	On State Collector Current	0.2	0.4		mA	Vce = 5V Ee=1mW/c m [°] λ=940nm
201/2	Angle of half sensitivity		120		deg	

Absolute Maximum Ratings at TA=25℃

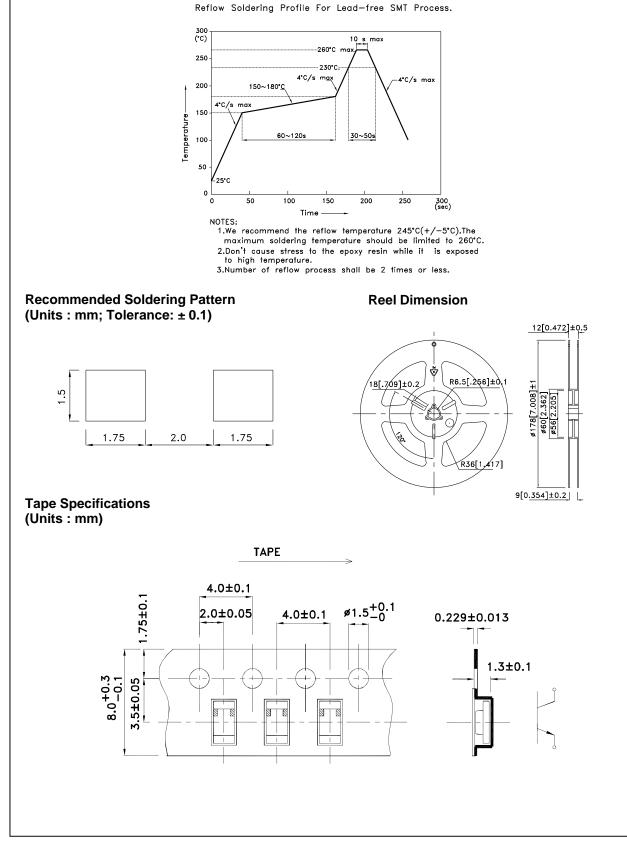
Parameter	Max.Ratings		
Collector-to-Emitter Voltage	30V		
Emitter-to-Collector Voltage	5V		
Power Dissipation at (or below) 25°C Free Air Temperature	100mW		
Operating Temperature	-40°C To +85°C		
Storage Temperature	-40°C To +85°C		



DATE: SEP/25/2012 DRAWN: D.M.Su

KP-3216P3C

Reflow soldering is recommended and the soldering profile is shown below. Other soldering methods are not recommended as they might cause damage to the product.



DATE: SEP/25/2012 DRAWN: D.M.Su

